







IF140, IF140A N-Channel JFET

Features

InterFET N0014L Geometry
Low Noise: 4 nV/VHz Typical
High Gain: 4.5mS Typical

Low Ciss: 3.0pF MaximumReplacement for IF142

RoHS Compliant

• SMT, TH, and Bare Die Package options.

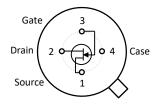
Applications

· Low Noise, High Gain Amplifiers

Description

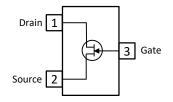
The -20V InterFET IF140 and IF140A are targeted for low noise high gain amplifier stages for mid to high frequencies designs. Gate leakages are typically 2pA at room temperatures. The TO-72 package is hermetically sealed and suitable for military applications.

TO-72 Bottom View





SOT23 Top View





Product Summary

Parameters		IF140 Min	IF140A Min	Unit	
BV _{GSS}	Gate to Source Breakdown Voltage	-20	-20	V	
I _{DSS}	Drain to Source Saturation Current	5	5	mA	
V _{GS(off)}	Gate to Source Cutoff Voltage	-0.3	-0.3	V	
GFS	Forward Transconductance	3.5	3.5	mS	

Ordering Information Custom Part and Binning Options Available

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Part Number	Description	Case	Packaging			
IF140T72; IF140AT72	Through-Hole	TO-72	Bulk			
IF140ST3; IF140AST3	Surface Mount	SOT23	Bulk			
	7" Tape and Reel: Max 3,000 Pieces		Minimum 1,000 Pieces			
IF140ST3TR; IF140AST3TR	13" Tape and Reel: Max 9,000 Pieces	SOT23	Tape and Reel			
IF140COT; IF140ACOT	Chip Orientated Tray (COT Waffle Pack)	COT	400/Waffle Pack			
IF140CFT; IF140ACFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack			



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.









Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

	Parameters	Value	Unit
V_{RGS}	Reverse Gate Source and Gate Drain Voltage	-20	V
I _{FG}	Continuous Forward Gate Current	10	mA
PD	Continuous Device Power Dissipation	375	mW
Р	Power Derating	3	mW/°C
Τı	Operating Junction Temperature	-55 to 125	°C
T _{STG}	Storage Temperature	-65 to 200	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

·			IF140		IF140A		
	Parameters	Conditions	Min	Max	Min	Max	Unit
V _{(BR)GSS}	Gate to Source Breakdown Voltage	V _{DS} = 0V, I _G = -1μA	-20		-20		V
I _{GSS}	Gate to Source Reverse Current	$V_{GS} = -15V$, $V_{DS} = 0V$, $T_A = 25$ °C $V_{GS} = -15V$, $V_{DS} = 0V$, $T_A = 150$ °C		-0.1 -0.2		-0.1 -0.2	nA nA
V _{GS(F)}	Gate to Source Forward Voltage	$V_{DS} = 0V, I_G = 1mA$		1		1	V
V _{GS(OFF)}	Gate to Source Cutoff Voltage	V _{DS} = 15V, I _D = 5nA		-6		-6	V
V _{GS}	Gate to Source Voltage	V _{DS} = 15V, I _D = 50μA		-5	-2.5	-6	V
I _{DSS}	Drain to Source Saturation Current	$V_{GS} = 0V$, $V_{DS} = 15V$ (Pulsed)	5	15	5	15	mA

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

			IF140		IF140A		
	Parameters	Conditions	Min	Max	Min	Max	Unit
G _{FS}	Forward Transconductance	V _{DS} = 15V, V _{GS} = 0V, f = 1kHz	3.5		3.5		mS
Gos	Output Conductance	V _{DS} = 15V, V _{GS} = 0V, f = 1kHz		0.05		0.05	mS
Ciss	Input Capacitance	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz		3		3	pF
Crss	Reverse Transfer Capacitance	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz		0.6		0.6	pF
e _n	Equivalent Circuit Input Noise Voltage	V _{DS} = 12V, V _{GS} = 0V, f = 10Hz	4 (t	4 (typ) 4 (typ)		typ)	nV/√Hz

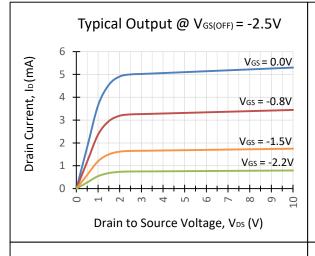


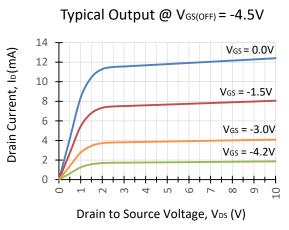


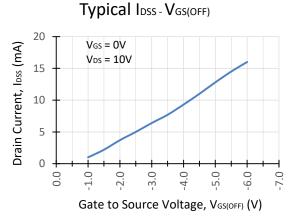


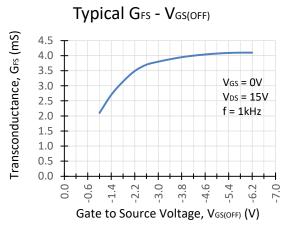


Typical IF140 Characteristics









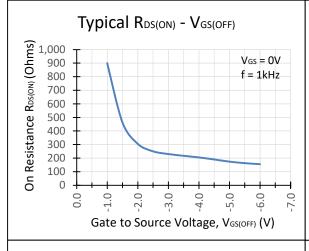


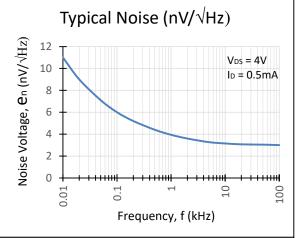


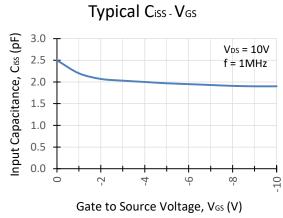


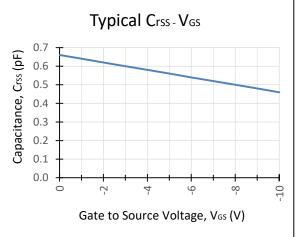


Typical IF140 Characteristics (Continued)











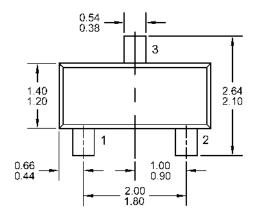


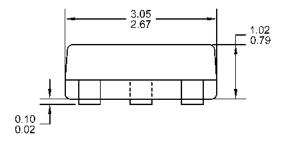


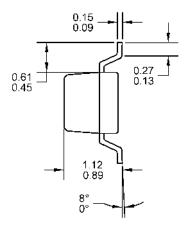


SOT23 (TO-236AB) Mechanical and Layout Data

Package Outline Data

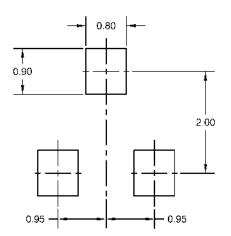






- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.12 grams
- 3. Molded plastic case UL 94V-0 rated
- For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
- Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

Suggested Pad Layout



- 1. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.



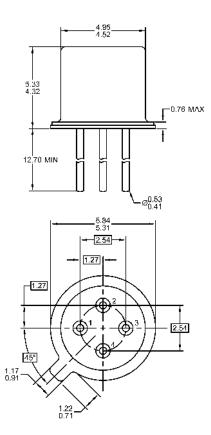






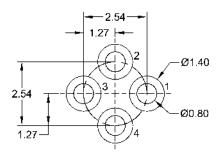
TO-72 Mechanical and Layout Data

Package Outline Data



- 1. All linear dimensions are in millimeters.
- Four leaded device. Not all leads are shown in drawing views.
- 3. Package weight approximately 0.31 grams
- Bulk product is shipped in standard ESD shipping material
- 5. Refer to JEDEC standards for additional information.

Suggested Through-Hole Layout



- 1. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.